

TO-18 Plastic-Encapsulate Transistors

D882 TRANSISTOR (NPN)

FEATURES

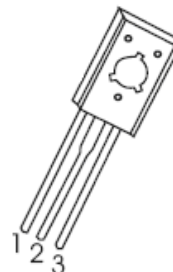
- Power Dissipation

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	3	A
P _C	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-18

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS (T_a=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _C = 100μA, I _E =0	40			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C = 10mA, I _B =0	30			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} = 40 V, I _E =0			1	μA
Collector cut-off current	I _{CEO}	V _{CE} = 30 V, I _B =0			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _C =0			1	μA
DC current gain	h _{FE}	V _{CE} = 2 V, I _C = 1A	60		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 2A, I _B = 0.2 A			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 2A, I _B = 0.2 A			1.5	V
Transition frequency	f _T	V _{CE} = 5V, I _C =0.1A f =10MHz		90		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

